Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-59. (Canceled)

60. (Previously Presented) A method of manufacturing a wiring substrate, comprising:

disposing first and second droplets over a substrate, the first and second droplets not being in contact with each other, each of the first and second droplets including a first solvent component and a first functional particle;

gasifying a first part of the first solvent component from each of the first and second droplets by irradiating the first and second droplets with a first light to form first and second applied films over the substrate, the first and second applied films not being in contact with each other, each of the first and second applied films including a second part of the first solvent component and the first functional particle;

disposing a third droplet between the first and second applied films, the third droplet contacting at least one of the first and second applied films, the third droplet including a second solvent component and a second functional particle;

gasifying a first part of the second solvent component from the third droplet by irradiating the third droplet with the first light to form a third applied film between the first and second applied films, the third applied film contacting at least one of the first and second applied films, the third applied film including a second part of the second solvent component and the second functional particle; and

excluding the second part of the first solvent component and the second part of the second solvent component from the first, second and third applied films by sintering the first, second and third applied films to form a functional material.

61. (Previously Presented) The method of manufacturing a wiring substrate according to claim 60, the process of sintering the first, second, and third applied films including irradiating the first, second, and third applied films with a second light, an intensity of the second light being higher than that of the first light.

62. (Previously Presented) The method of manufacturing a wiring substrate according to claim 60, each of the first and second applied films including a coating film that coats the first functional particle, the coating film being removed at the process of sintering the first, second, and third applied films.

63. (Previously Presented) The method of manufacturing a wiring substrate according to claim 60, the first and second droplets being discharged by a first head of an inkjet apparatus.

64. (Previously Presented) The method of manufacturing a wiring substrate according to claim 60, the first and second droplets being discharged by a first head of an inkjet apparatus, the third droplet being discharged by a second head of an inkjet apparatus.

65. (Previously Presented) The method of manufacturing a wiring substrate according to claim 60, the first light being a wide beam that is correspondingly beamed to the first and second droplets.

66. (Previously Presented) The method of manufacturing a wiring substrate according to claim 60, the first light being beamed to the first and the second droplets through a diffraction optical element.

67. (Previously Presented) The method of manufacturing a wiring substrate according to claim 60, the first light being reflected by a reflector before the first light is beamed to the first and second droplets.

68. (Previously Presented) The method of manufacturing a wiring substrate according to claim 60, the substrate being made of a transparent material, the first light

passing from a second surface of the substrate to a first surface of the substrate, the first and the second droplets being disposed over the first surface of the substrate.

69. (Previously Presented) The method of manufacturing a wiring substrate according to claim 60, a viscosity of the first droplet being lower than that of the first applied film.

70. (Previously Presented) The method for manufacturing a wiring substrate according to claim 60, each of the first and second droplets including a photothermal conversion material that has an absorption band in the wavelength region of the first light.

71. (Previously Presented) A method of manufacturing a wiring substrate, comprising:

disposing a first droplet over a substrate, the first droplet including a first solvent component and a first functional particle;

gasifying a first part of the first solvent component from the first droplet by irradiating the first droplet with a first light to form a first applied film over the substrate, the first applied film including a second part of the first solvent component and the first functional particle;

disposing a second droplet over the substrate, the second droplet contacting at least a part of the first applied film, the second droplet including a second solvent component and a second functional particle;

gasifying a first part of the second solvent component from the second droplet by irradiating the second droplet with the first light to form a second applied film over the substrate, the second applied film contacting at least a part of the first applied film, the second applied film including a second part of the second solvent component and the second functional particle;

excluding the second part of the first solvent component and the second part of the second solvent component from the first and second applied films by sintering the first and second applied films to form a functional material.

72. (Previously Presented) The method of manufacturing a wiring substrate according to claim 71, the process of sintering the first and second applied films including irradiating the first and second applied films with a second light, an intensity of the second light being higher than that of the first light.

73. (New) The method of manufacturing a wiring substrate, comprising:

disposing a plurality of first droplets over a substrate, each of the first droplets not being in contact with each other, and each of the first droplets including a first solvent and first particles;

forming first applied films by irradiating the first droplets with a first light;

disposing a plurality of second droplets between the first applied films over the substrate, each of the second droplets not being in contact with each other, and each of the second droplets including a second solvent and second particles;

forming second applied films by irradiating the second droplets with a second light;

disposing a plurality of third droplets between the second applied films over the substrate, each of the third droplets not being in contact with each other, and each of the third droplets including a third solvent and third particles;

forming third applied films by irradiating the third droplets with a third light;

disposing a plurality of fourth droplets between the third applied films over the substrate, each of the fourth droplets not being in contact with each other, and each of the fourth droplets including a fourth solvent and fourth particles;

forming fourth applied films by irradiating the fourth droplets with a fourth light;

disposing a plurality of fifth droplets between the fourth applied films over the substrate, each of the fifth droplets not being in contact with each other, and each of the fifth droplets including a fifth solvent and fifth particles; and

forming a functional material by sintering the first applied films, the second applied films, the third applied films, the fourth applied films and the fifth droplets with a fifth light, wherein:

each of the applied films are gasified by gasifying each of the solvent from each of the droplets by irradiation, and

displacement of each of the particles in the applied films from a disposed position of the each of the particles in the droplets being adjusted to not more than 1/5 of a diameter of each of the droplets.

74. (New) The method of manufacturing a wiring substrate, comprising:

disposing a plurality of first droplets over a substrate, each the first droplets not being in contact with each other, and each of the first droplets including a first solvent and first particles;

forming first applied films by irradiating the first droplets with a first light;

disposing a plurality of second droplets between the first applied films over the substrate, each of the second droplets not being in contact with each other, and each of the second droplets including a second solvent and second particles;

forming second applied films by irradiating the second droplets with a second light;

disposing a plurality of third droplets between the second applied films over the substrate, each of the third droplets not being in contact with each other, and each of the third droplets including a third solvent and third particles;

forming third applied films by irradiating the third droplets with a third light;

disposing a plurality of fourth droplets between the third applied films over the substrate, each of the fourth droplets not being in contact with each other, and each of the fourth droplets including a fourth solvent and fourth particles;

forming fourth applied films by irradiating the fourth droplets with a fourth light;

disposing a plurality of fifth droplets between the fourth applied films over the substrate, each of the fifth droplets not being in contact with each other, and each of the fifth droplets including a fifth solvent and fifth particles; and

forming a functional material by sintering the first applied films, the second applied films, the third applied films, the fourth applied films and the fifth droplets with a fifth light, wherein:

each of the first applied films are gasified by gasifying the first solvent from each of the first droplets by irradiation with the first light,

displacement of each of the first particles in each of the first applied films from a disposed position of the each of the first particles in each of the first droplets being adjusted to not more than 1/5 of a diameter of each of the first droplets,

each of the second applied films are gasified by gasifying the second solvent from each of the second droplets by irradiation with the second light,

displacement of each of the second particles in each of the second applied films from a disposed position of the each of the second particles in each of the

second droplets being adjusted to not more than 1/5 of a diameter of each of the second droplets,

each of the third applied films are gasified by gasifying the third solvent from each of the third droplets by irradiation with the third light,

displacement of each of the third particles in each of the third applied films from a disposed position of the each of the third particles in each of the third droplets being adjusted to not more than 1/5 of a diameter of each of the third droplets,

each of the fourth applied films are gasified by gasifying the fourth solvent from each of the fourth droplets by irradiation with the fourth light, and

displacement of each of the fourth particles in each of the fourth applied films from a disposed position of the each of the fourth particles in each of the fourth droplets being adjusted to not more than 1/5 of a diameter of each of the fourth droplets.